L	Hits	Search Text	DB	Time stamp
Number				
1	448237	through adj hole	USPAT;	2003/12/03
			US-PGPUB;	19:43
	ļ		EPO; JPO;	
			DERWENT;	
2	1677983	substrate	IBM_TDB	
2	10//903	Substrate	USPAT;	2003/12/03
			US-PGPUB;	19:41
			EPO; JPO; DERWENT;	
			IBM TDB	
3	26879	(through adj hole) with substrate	USPAT;	2003/12/03
		, was any state, which have stated	US-PGPUB;	19:42
			EPO; JPO;	13.12
			DERWENT;	
			IBM TDB	
4	64608	anodi\$8	USPĀT;	2003/12/03
			US-PGPUB;	19:42
			EPO; JPO;	
			DERWENT;	
5	626	//*************************************	IBM_TDB	
]]	020	((through adj hole) with substrate) and anodi\$8	USPAT;	2003/12/03
		anouișo	US-PGPUB;	19:42
			EPO; JPO;	
			DERWENT; IBM TDB	
6	448237	through adj1 hole	USPAT;	2003/12/03
			US-PGPUB;	19:43
			EPO; JPO;	19.43
			DERWENT;	
			IBM TDB	
7	626	((through adj1 hole) with substrate) and	USPAT;	2003/12/03
		anodi\$8	US-PGPUB;	19:44
			EPO; JPO;	
			DERWENT;	
8	0	///thmough add 1 halas add	IBM_TDB	
1	١	(((through adj1 hole) with substrate) and anodi\$8) not (((through adj hole) with	USPAT;	2003/12/03
		substrate) and anodi\$8)	US-PGPUB;	19:44
		bassing of and amounts)	EPO; JPO; DERWENT;	
			IBM TDB	
9	79	(((through adj1 hole) with substrate) and	USPAT;	2003/12/03
		anodi\$8) and 438/\$.ccls.	US-PGPUB;	19:45
			EPO; JPO;	20010
			DERWENT;	
	5060	(///20///66)	IBM_TDB	,
-	5063	((438/466) or (438/469) or (438/599) or	USPAT;	2003/12/03
		(438/620) or (438/631) or (438/633) or	US-PGPUB;	00:16
		(438/666) or (438/667) or (438/690) or (438/691) or (438/692) or (438/693) or	EPO; JPO;	
		(438/928) or (438/977)).CCLS.	DERWENT;	
	52	(((438/466) or (438/469) or (438/599) or	IBM_TDB USPAT;	2002/12/02
		(438/620) or (438/631) or (438/633) or	US-PGPUB;	2003/12/03 01:52
		(438/666) or (438/667) or (438/690) or	EPO; JPO;	01.32
		(438/691) or (438/692) or (438/693) or	DERWENT;	
		(438/928) or (438/977)).CCLS.) and	IBM TDB	
		((anodic or anodiz\$5) same oxide)		
-	24	((((438/466) or (438/469) or (438/599) or	USPAT;	2003/12/03
		(438/620) or (438/631) or (438/633) or	US-PGPUB;	00:19
	İ	(438/666) or (438/667) or (438/690) or	EPO; JPO;	
		(438/691) or (438/692) or (438/693) or	DERWENT;	
		(438/928) or (438/977)).CCLS.) and ((anodic or anodiz\$5) same oxide)) and	IBM_TDB	
		((rear or back) same surface)		
		(\Iour or back) same Surrace)		

	,			
_	22	((((438/466) or (438/469) or (438/599) or (438/620) or (438/631) or (438/633) or (438/666) or (438/667) or (438/690) or (438/691) or (438/692) or (438/693) or (438/928) or (438/977)).CCLS.) and ((anodic or anodiz\$5) same oxide)) and ((rear or back) same surface same (wafer or substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 00:54
-	2	(((((438/466) or (438/469) or (438/599) or (438/620) or (438/631) or (438/633) or (438/666) or (438/667) or (438/690) or (438/691) or (438/692) or (438/693) or (438/928) or (438/977)).CCLS.) and ((anodic or anodiz\$5) same oxide)) and ((rear or back) same surface)) not (((((438/466) or (438/469) or (438/599)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 00:26
	28	or (438/620) or (438/631) or (438/633) or (438/666) or (438/667) or (438/690) or (438/691) or (438/692) or (438/693) or (438/928) or (438/977)).CCLS.) and ((anodic or anodiz\$5) same oxide)) and ((rear or back) same surface same (wafer or substrate))) (((438/466) or (438/469) or (438/599) or	исрът.	2002/12/02
	20	(438/620) or (438/631) or (438/633) or (438/666) or (438/667) or (438/690) or (438/666) or (438/667) or (438/690) or (438/691) or (438/692) or (438/693) or (438/928) or (438/977)).CCLS.) and ((anodic or anodiz\$5) same oxide)) not (((((438/466) or (438/469) or (438/539) or (438/660) or (438/631) or (438/633) or (438/666) or (438/667) or (438/690) or (438/691) or (438/928) or (438/977)).CCLS.) and ((anodic or anodiz\$5) same oxide)) and ((rear or back) same surface))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03
-	6075	((438/408) or (438/430) or (438/431) or (438/432) or (438/719) or (438/735) or (438/738) or (438/750) or (438/751) or (438/753) or (438/756) or (438/762) or (438/769) or (438/770) or (438/771) or (438/772) or (438/773) or (438/774) or (438/787) or (438/788) or (438/928) or (438/959) or (438/977)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 00:37
	128	(((438/408) or (438/430) or (438/431) or (438/432) or (438/719) or (438/735) or (438/738) or (438/750) or (438/751) or (438/753) or (438/756) or (438/762) or (438/769) or (438/770) or (438/771) or (438/772) or (438/773) or (438/774) or (438/787) or (438/788) or (438/928) or (438/959) or (438/977)).CCLS.) and ((anodic or anodiz\$5) same oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 00:37
	106	((((438/408) or (438/430) or (438/431) or (438/432) or (438/719) or (438/735) or (438/738) or (438/750) or (438/751) or (438/753) or (438/756) or (438/751) or (438/753) or (438/756) or (438/762) or (438/770) or (438/771) or (438/772) or (438/773) or (438/774) or (438/787) or (438/788) or (438/928) or (438/959) or (438/977)).CCLS.) and ((anodic or anodiz\$5) same oxide)) not ((((438/466) or (438/469) or (438/599) or (438/620) or (438/631) or (438/666) or (438/667) or (438/693) or (438/691) or (438/692) or (438/693) or (438/928) or (438/977)).CCLS.) and ((anodic or anodiz\$5) same oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 00:53

_	1523	438/\$.ccls. and ((anodic or anodiz\$5)	1,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	
	1323	same oxide)	USPAT;	2003/12/03
		Same Oxide)	US-PGPUB;	00:54
			EPO; JPO;	1
			DERWENT;	
_	894	//20/0 ==1	IBM_TDB	
-	094		USPAT;	2003/12/03
		same oxide)) and ((anodic or anodiz\$5)	US-PGPUB;	00:56
	į	same oxide same (wafer or substrate))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	566		USPAT;	2003/12/03
		same oxide)) and ((anodic or anodiz\$5)	US-PGPUB;	00:57
		same oxide same (wafer or substrate)))	EPO; JPO;	
		and (hole or via or (contact adj hole) or	DERWENT;	
		(through adj hole))	IBM TDB	
-	498	((438/\$.ccls. and ((anodic or anodiz\$5)	USPĀT;	2003/12/03
		same oxide)) and ((anodic or anodiz\$5)	US-PGPUB;	00:58
		same oxide same (wafer or substrate)))	EPO; JPO;	
1		and ((substrate or wafer) same (hole or	DERWENT;	
	i	via or (contact adj hole) or (through adj	IBM TDB	
		hole) or opening))		
-	457	(((438/\$.ccls. and ((anodic or anodiz\$5)	USPAT;	2003/12/03
		same oxide)) and ((anodic or anodiz\$5)	US-PGPUB;	00:58
		same oxide same (wafer or substrate)))	EPO; JPO;	00.00
		and ((substrate or wafer) same (hole or	DERWENT;	
		via or (contact adj hole) or (through adj	IBM TDB	
		hole) or opening))) and (electrode or	1511_100	
		plug or conduct\$3)		
-	196	(((438/\$.ccls. and ((anodic or anodiz\$5)	USPAT;	2003/12/03
1		same oxide)) and ((anodic or anodiz\$5)	US-PGPUB;	01:47
		same oxide same (wafer or substrate)))	EPO; JPO;	01.47
		and ((substrate or wafer) same (hole or	DERWENT;	
		via or (contact adj hole) or (through adj	IBM TDB	
		hole) or opening))) and ((expos\$3 or	1 DM _ 1 DB	
		protrud\$3) same (electrode or plug or		
		conduct\$3) same (substrate or wafer))		
-	115	(NEMOTO same YOSHIHIKO) OR (HOSHINO same	IICDAM.	2002/12/02
		MASATAKA) OR (YONEMURA same HITOSHI)	USPAT;	2003/12/03
			US-PGPUB;	01:52
			EPO; JPO; DERWENT;	
1				
] _	0	((NEMOTO same YOSHIHIKO) OR (HOSHINO same	IBM_TDB	2002/12/22
	١ "	MASATAKA) OR (YONEMURA same HITOSHI)) and	USPAT;	2003/12/03
		((anodic or anodiz\$5) same oxide)	US-PGPUB;	01:52
		((amound of amounday)) same oxide)	EPO; JPO;	
		İ	DERWENT;	
_	1	((NEMOTO same VOCHILIVO) OR (MOCATIVE	IBM_TDB	
	-	((NEMOTO same YOSHIHIKO) OR (HOSHINO same	USPAT;	2003/12/03
	İ	MASATAKA) OR (YONEMURA same HITOSHI)) and (anodic or anodiz\$5)	US-PGPUB;	19:41
		(anoute of anoutz33)	EPO; JPO;	
			DERWENT;	1
L			IBM_TDB	